

Dmitry Gorshkov

List of Publications by Year in descending order

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Version: 2024-02-01

12
papers

48
citations

1684188

5
h-index

1720034

7
g-index

12
all docs

12
docs citations

12
times ranked

56
citing authors

#	ARTICLE	IF	CITATIONS
1	Evolution of the transverse and longitudinal energy distributions of electrons emitted from a GaAsP photocathode as a function of its degradation state. Journal of Applied Physics, 2017, 121, .	2.5	12
2	The Effect of the Growth Temperature on the Passivating Properties of the Al ₂ O ₃ Films Formed by Atomic Layer Deposition on the CdHgTe Surface. Technical Physics Letters, 2020, 46, 741-744.	0.7	7
3	Optical phonon cascade emission by photoelectrons at a p-GaN (Cs,O)-vacuum interface. JETP Letters, 2016, 104, 135-139.	1.4	6
4	Photodetectors with 384 × 288 Matrix Elements for the Infrared Range of 8–10 Microns. Journal of Communications Technology and Electronics, 2019, 64, 1024-1029.	0.5	6
5	Surface photovoltage in a p-GaN(Cs) photocathode. Journal of Physics: Conference Series, 2019, 1199, 012031.	0.4	6
6	A Megapixel Matrix Photodetector of the Middle Infrared Range. Journal of Communications Technology and Electronics, 2019, 64, 1011-1015.	0.5	5
7	Surface Conductivity Dynamics in PbSnTe:In Films in the Vicinity of a Band Inversion. Semiconductors, 2019, 53, 1182-1186.	0.5	2
8	Reconversion of the CdHgTe conductivity type after plasma etching process at low temperature. Applied Physics Letters, 2020, 116, 082102.	3.3	2
9	Effect of Surface Treatment on the Charge Density at the Interface between GdHgTe Epitaxial Films and Al ₂ O ₃ Grown by Atomic Layer Deposition. Optoelectronics, Instrumentation and Data Processing, 2020, 56, 492-497.	0.6	2
10	Study of the Density of Interface States at the Insulator/In _{0.52} Al _{0.48} As Interface. Technical Physics Letters, 2020, 46, 469-472.	0.7	0
11	Features of MIS Structures Based on Insulating PbSnTe:In Films with the Composition in the Vicinity of the Band Inversion Related to Their Ferroelectric Properties. Semiconductors, 2020, 54, 1325-1331.	0.5	0
12	Al ₂ O ₃ /InGaAs interface passivation by fluorine-containing anodic layers. Journal of Applied Physics, 2022, 131, 085301.	2.5	0